

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	160	((438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and ((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp)) and (ion near implant\$8)) and (sac (aligned adj contact))	US-PGPUB; USPAT	OR	ON	2005/02/02 16:20
L2	1	"6649500".URPN.	USPAT	OR	OFF	2005/02/02 16:29
L3	2	"6268272".URPN.	USPAT	OR	OFF	2005/02/02 16:30
L4	1	"6255206".URPN.	USPAT	OR	OFF	2005/02/02 16:30
L5	171	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp same (ion near implant\$8) same ((contact adj (opening hole via)) plug ((conduct\$6 metal) near via) sac (aligned adj contact)) same (gate source drain) same (sidewall spacer silicide (side adj wall))	US-PGPUB; USPAT	OR	ON	2005/02/02 16:31
L6	205	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and (ion near implant\$8) and ((contact adj (opening hole via)) plug ((conduct\$6 metal) near via)) and (gate source drain sidewall spacer silicide (side adj wall))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:39
L7	281	(438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and ((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and ((ion near implant\$8) with (argon nitrogen oxygen))	US-PGPUB; USPAT	OR	ON	2005/02/02 16:55
L8	265	7 and (gate transistor \$3fet \$1mos (field adj effect))	US-PGPUB; USPAT	OR	ON	2005/02/02 16:54
L9	146	(438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and ((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and (((ion near implant\$8) with (argon nitrogen oxygen)) same (gate transistor \$3fet \$1mos (field adj effect)))	US-PGPUB; USPAT	OR	ON	2005/02/02 17:53

L10	263	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) same (((ion near implant\$8) with (argon nitrogen oxygen)) same (gate transistor \$3fet \$1mos (field adj effect)))	US-PGPUB; USPAT	OR	ON	2005/02/02 17:52
L11	118	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and (((ion near implant\$8) with (argon nitrogen oxygen)) and (gate transistor \$3fet \$1mos (field adj effect)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 17:51
L12	188	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and ((implant\$8 with (argon nitrogen oxygen)) and (gate transistor \$3fet \$1mos (field adj effect)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 17:51
L13	317	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) same ((implant\$8 near2 (argon nitrogen oxygen)) same (gate transistor \$3fet \$1mos (field adj effect)))	US-PGPUB; USPAT	OR	ON	2005/02/02 17:53
L14	147	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) same ((implant\$8 near2 (argon nitrogen oxygen)) with (gate transistor \$3fet \$1mos (field adj effect)))	US-PGPUB; USPAT	OR	ON	2005/02/02 18:13
L15	94	(438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and (((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) same ((implant\$8 with (argon nitrogen oxygen)) same (gate transistor \$3fet \$1mos (field adj effect))))	US-PGPUB; USPAT	OR	ON	2005/02/02 17:55